**Preferred Device** 

# **General Purpose Transistors**

# **PNP Silicon**

### **Features**

• Pb-Free Packages are Available\*

# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	40	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	600	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

# THERMAL CHARACTERISTICS

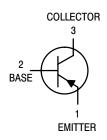
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

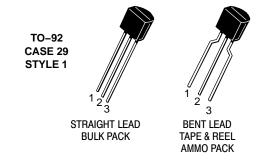
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



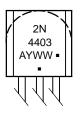
# ON Semiconductor®

http://onsemi.com





# **MARKING DIAGRAM**



2N4403 = Device Code A = Assembly Location

Y = Year WW = Work Week ■ Pb–Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		•	•
Collector-Emitter Breakdown	n Voltage (Note 1)	$(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	40	_	Vdc
Collector-Base Breakdown	/oltage	$(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V <sub>(BR)CBO</sub>	40	_	Vdc
Emitter-Base Breakdown Vo	ltage	$(I_E = 0.1 \text{ mAdc}, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	-	Vdc
Base Cutoff Current		(V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>BEV</sub>	-	0.1	μAdc
Collector Cutoff Current		(V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>CEX</sub>	-	0.1	μAdc
ON CHARACTERISTICS						
DC Current Gain		$ \begin{array}{c} (I_{C}=0.1 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=1.0 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=10 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \\ (I_{C}=150 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \text{ (Note 1)} \\ (I_{C}=500 \text{ mAdc, } V_{CE}=2.0 \text{ Vdc}) \text{ (Note 1)} \end{array} $	h <sub>FE</sub>	30 60 100 100 20	- - 300 -	-
Collector-Emitter Saturation	Voltage (Note 1)	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V <sub>CE(sat)</sub>	- -	0.4 0.75	Vdc
Base-Emitter Saturation Volt	tage (Note 1)	$(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V <sub>BE(sat)</sub>	0.75 -	0.95 1.3	Vdc
SMALL-SIGNAL CHARACT	ERISTICS					
Current-Gain - Bandwidth P	roduct (I	C = 20 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)	f <sub>T</sub>	200	_	MHz
Collector-Base Capacitance		(V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	-	8.5	pF
Emitter-Base Capacitance		$(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C <sub>eb</sub>	-	30	pF
Input Impedance	(	$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h <sub>ie</sub>	1.5 k	15 k	Ω
Voltage Feedback Ratio	(	$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$	h <sub>re</sub>	0.1	8.0	X 10 <sup>-4</sup>
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)		h <sub>fe</sub>	60	500	-	
Output Admittance ( $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$ )			h <sub>oe</sub>	1.0	100	μmhos
SWITCHING CHARACTERIS	STICS					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE} = +2.0 \text{ Vdc},$ $I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$		t <sub>d</sub>	-	15	ns
Rise Time			t <sub>r</sub>	-	20	ns
Storage Time	(V <sub>CC</sub> = 30 Vdc, I <sub>C</sub>	; = 150 mAdc,	t <sub>s</sub>	-	225	ns
Fall Time	$I_{B1} = 15 \text{ mA}, I_{B2} =$	= 15 mA)	t <sub>f</sub>	-	30	ns

<sup>1.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
2N4403	TO-92	5000 Units / Bulk
2N4403G	TO-92 (Pb-Free)	5000 Units / Bulk
2N4403RLRA	TO-92	2000 / Tape & Reel
2N4403RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N4403RLRM	TO-92	2000 / Ammo Pack
2N4403RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N4403RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# SWITCHING TIME EQUIVALENT TEST CIRCUIT

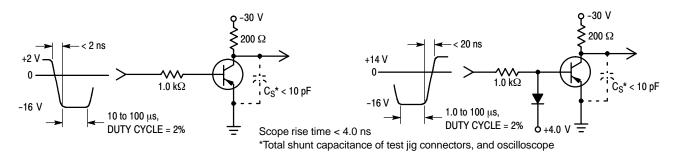


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

# TRANSIENT CHARACTERISTICS

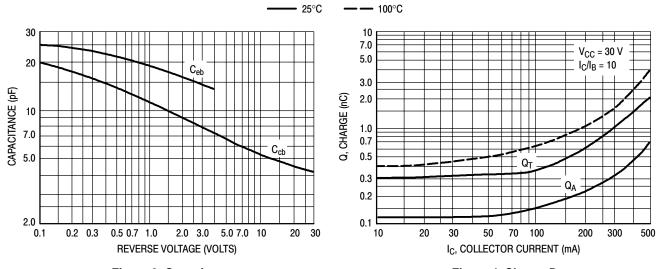
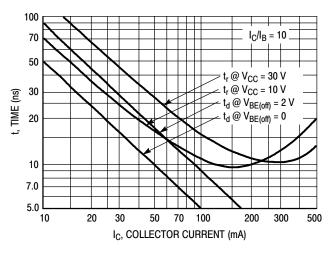


Figure 3. Capacitances

Figure 4. Charge Data



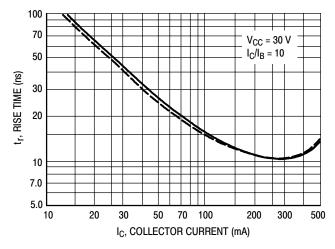


Figure 5. Turn-On Time

Figure 6. Rise Time

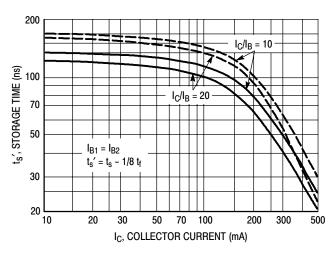
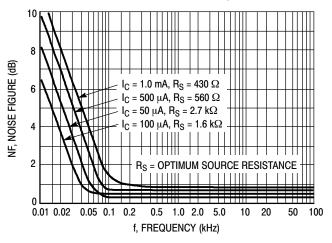


Figure 7. Storage Time

# SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE





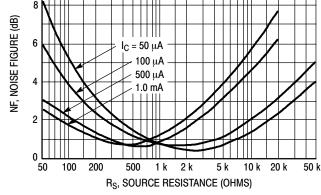


Figure 8. Frequency Effects

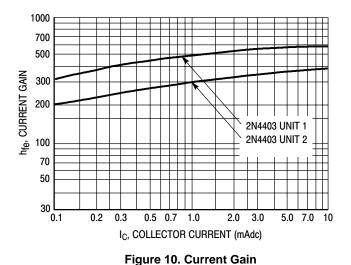
Figure 9. Source Resistance Effects

# h PARAMETERS

 $V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$ 

This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were

selected from the 2N4403 lines, and the same units were used to develop the correspondingly–numbered curves on each graph.



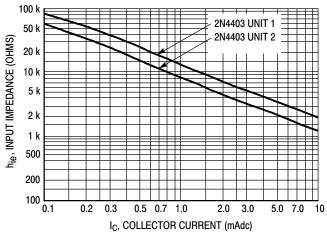


Figure 11. Input Impedance

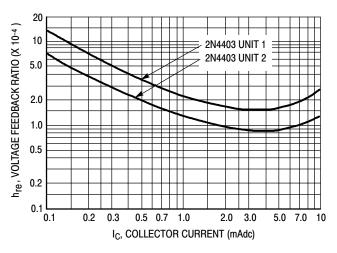


Figure 12. Voltage Feedback Ratio

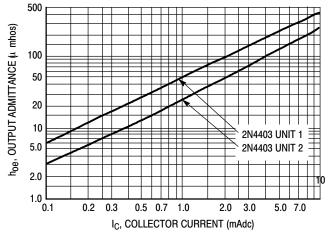


Figure 13. Output Admittance

# STATIC CHARACTERISTICS

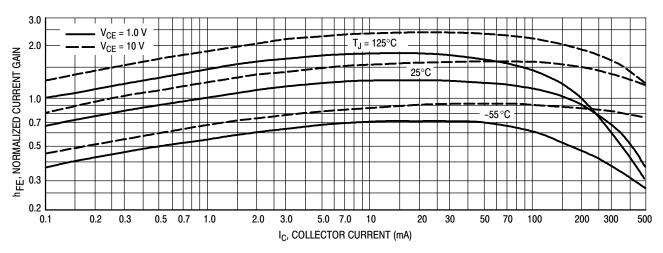


Figure 14. DC Current Gain

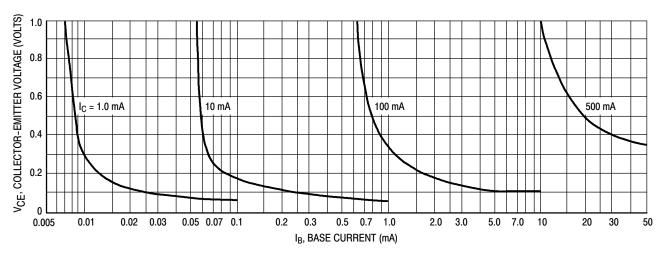


Figure 15. Collector Saturation Region

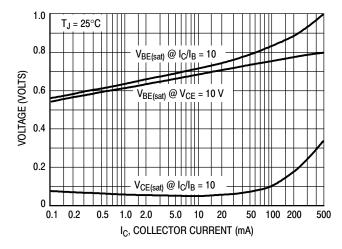
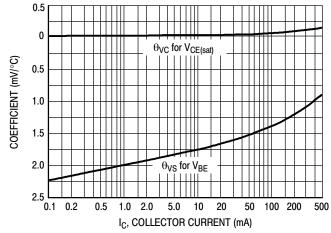


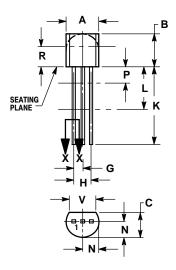
Figure 16. "On" Voltages



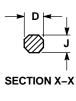
**Figure 17. Temperature Coefficients** 

### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



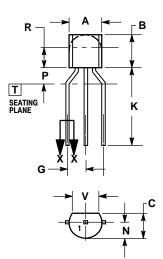
STRAIGHT LEAD **BULK PACK** 



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
  IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0 135		3 43	



**BENT LEAD TAPE & REEL** AMMO PACK



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION R IS UNCONTROLLED.

  LEAD DIMENSION IS UNCONTROLLED IN
- P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93	-	
٧	3.43		

PIN 1. EMITTER

BASE

COLLECTOR

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